2SA1930

Rev.F Mar.-2016

DATA SHEET

/ Descriptions

Silicon PNP transistor in a TO-220F Plastic Package.

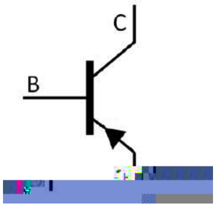
/ Features

High f_T, complementary pair with 2SC5171.

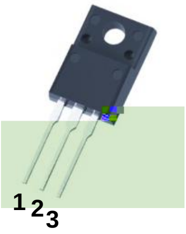
/ Applications

General power and driver stage amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1	Base	PIN 2	Collector	PIN 3	Emitter

/ h_{FE} Classifications & Marking

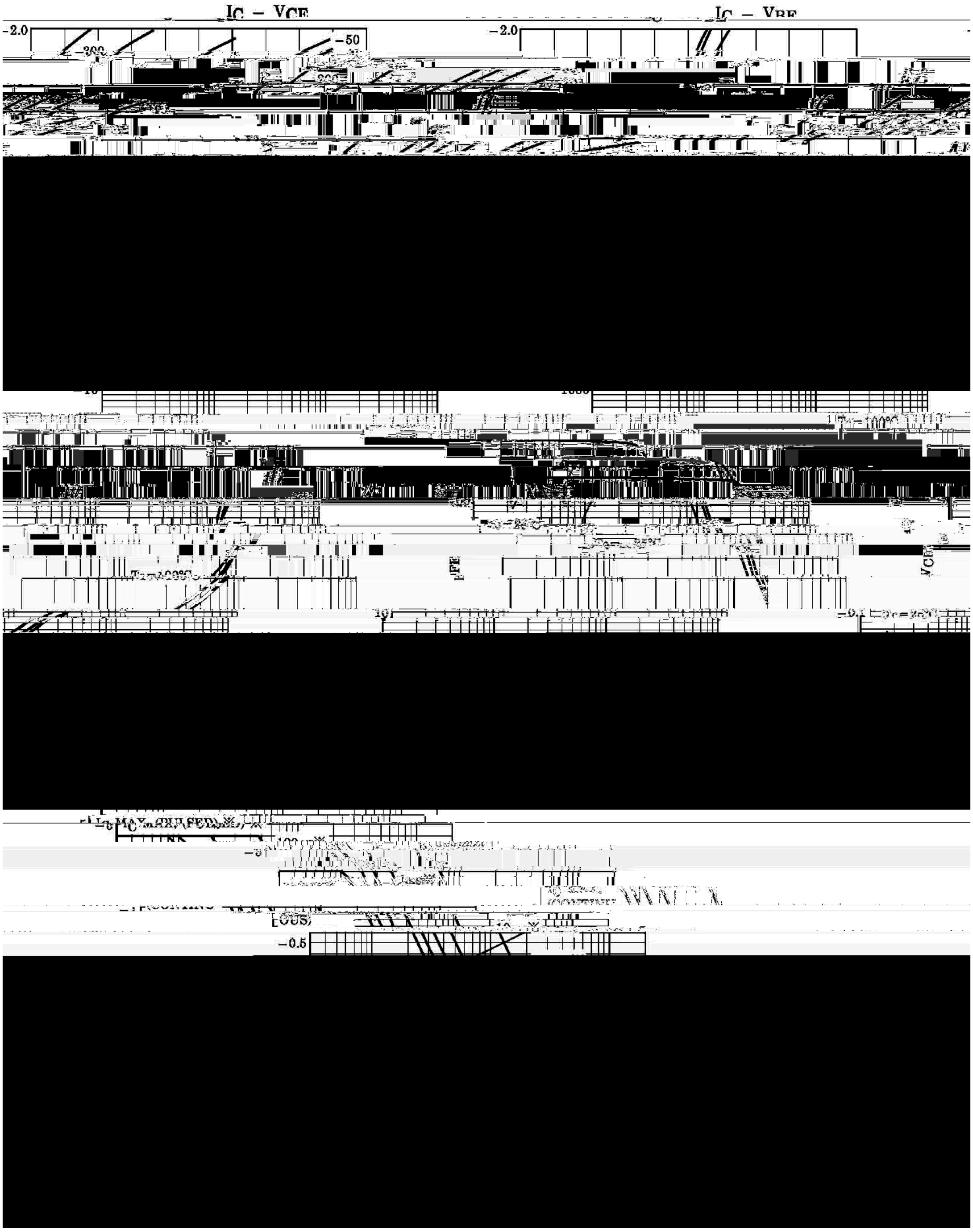
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-180	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Base Current	I_B	-1.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

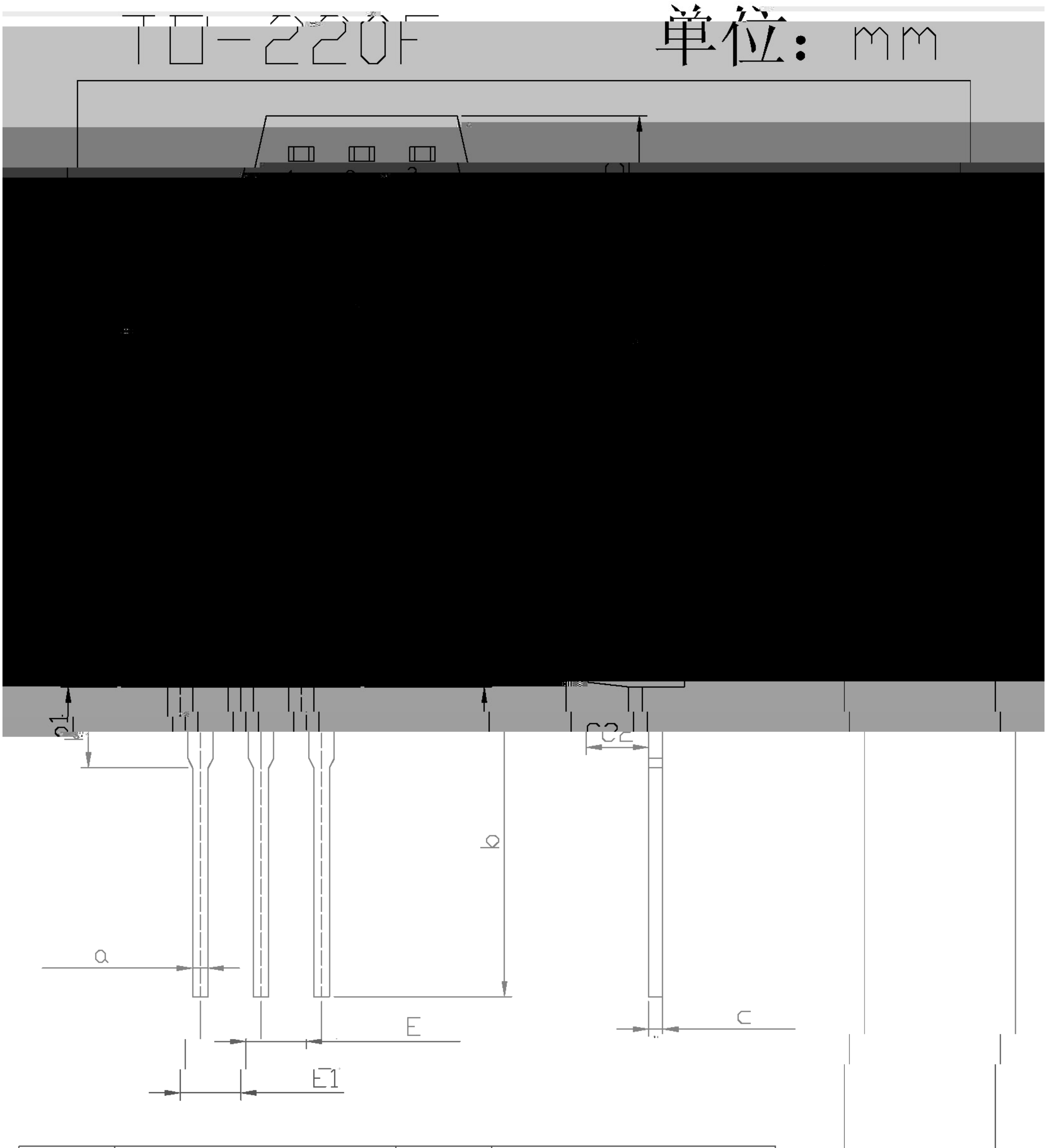
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-180			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-180V I_E=0			-5.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-5.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-5.0V I_C=-100mA	100		320	
	$h_{FE(2)}$	V_{CE}=-5.0V I_C=-1.0A	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1.0A I_B=-100mA		0310.0054		Tc01 18.

[redacted]

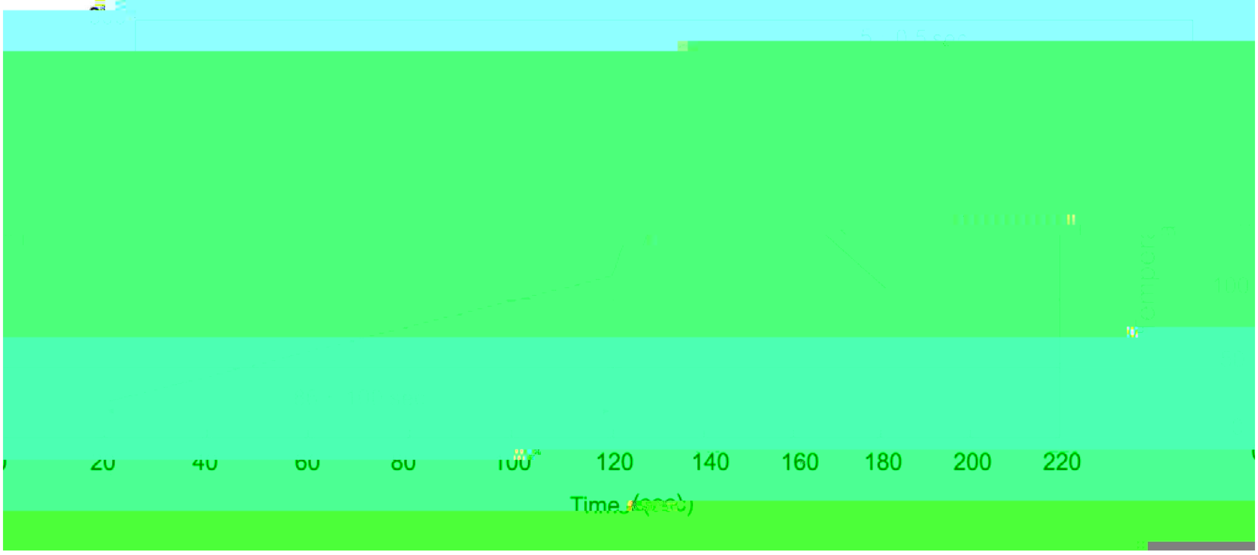
/ Electrical Characteristic Curve



/ Package Dimensions



(　　) / Temperature Profile for Dip Soldering(Pb-Free)



1　　25　150　　60　90sec;
2　　255　5　　5　0.5sec;
3　　2　10　/sec.

Note:
1.Preheating:25~150　, Time:60~90sec.
2.Peak Temp.:255　5　, Duration:5　0.5sec.
3. Cooling Speed: 2~10　/sec.

5　　255